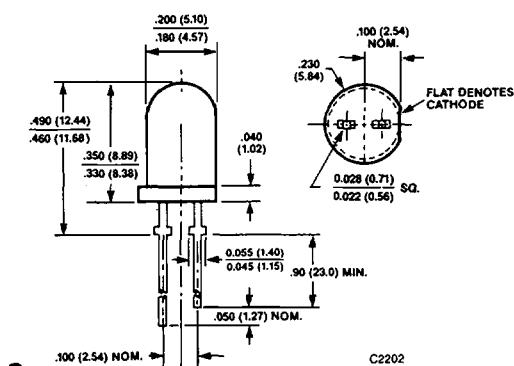
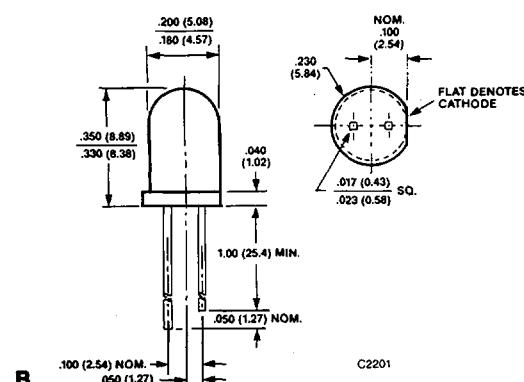
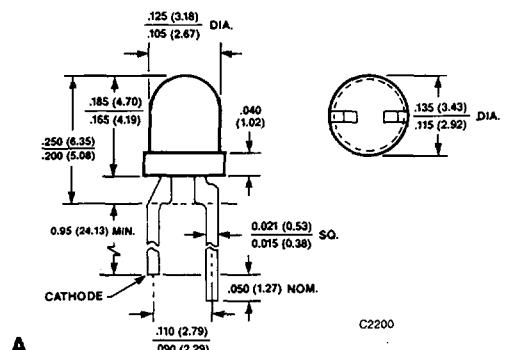


**T-1 $\frac{3}{4}$ HLMP-D150/D155
T-1 HLMP-K150/K155**
PACKAGE DIMENSIONS


1. ALL DIMENSIONS ARE IN INCHES (mm)
2. TOLERANCES ARE $\pm .005$ UNLESS OTHERWISE SPECIFIED
3. AN EPOXY MENISCUS MAY EXTEND ABOUT $.040^{\circ}$ (1 mm) DOWN THE LEADS

DESCRIPTION

A recently developed double heterojunction (DH) AlGaAs/GaAs material technology is the basis of the light emitting chip utilized in these solid state lamps. Exceptional light output typifies these devices and provides for their use over a broad range of drive currents. At a dominant wavelength of 637 nanometers, the light is perceived as a deep red color. These lamps are ideally suited for use in applications where high light output is required with minimum power input.

5
FEATURES

- Luminous intensity specified at 1 mA
- High light output at low currents
- Wide viewing angle
- Low power/low forward voltage
- Outstanding material efficiency
- CMOS/MOS compatible
- TTL compatible
- Deep red color

APPLICATIONS

- Low power circuits
- Battery powered equipment
- Telecommunication indicators

HLMP-D150/D155 HLMP-K150/K155

PHYSICAL CHARACTERISTICS

SIZE	TYPE	LENS EFFECT	I _V (mcd) MIN.	@ 1mA TYP.	VIEWING ANGLE 2Ø1/2 DEGREES	PKG.
T-1	HLMP-K150	Red Tinted Diffused	1.2	2	60	A
T-1	HLMP-K155	Clear	2	3	45	A
T-1½	HLMP-D150	Red Tinted Diffused	1.2	3	65	B
T-1½	HLMP-D155	Clear	5	10	24	C

ELECTRO-OPTICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

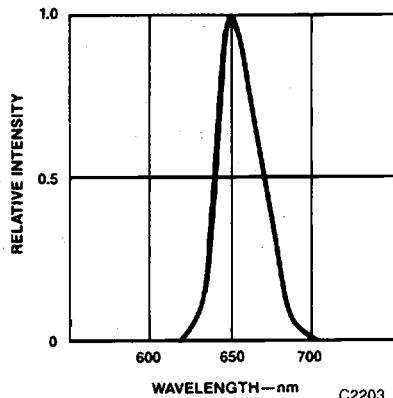
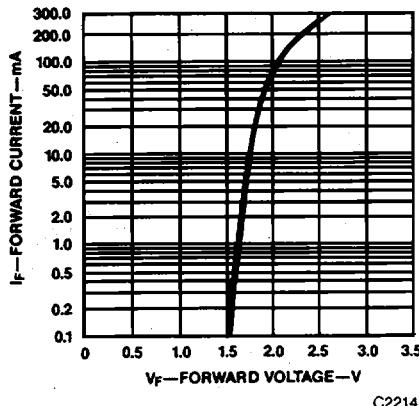
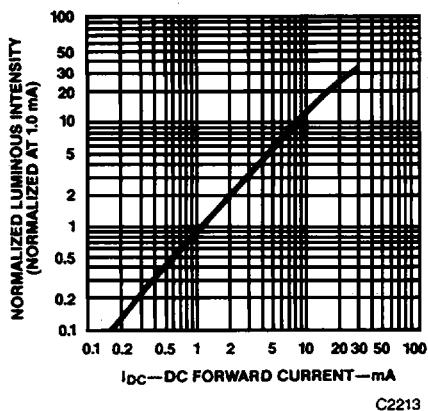
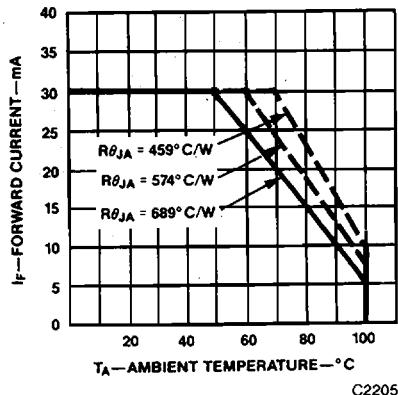
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Forward voltage	V _F	1.6	1.8		V	I _F =1 mA
Peak wavelength	λ_p	645			nm	I _F =1 mA
Dominant wavelength	λ_d	637			nm	I _F =1 mA
Spectral line half width	$\Delta\lambda_{1/2}$	20			nm	I _F =1 mA
Capacitance	C	30			pF	V _F =0, f=1 MHz
Reverse breakdown voltage	V _R	5.0	15.0		V	I _R =100 μ A

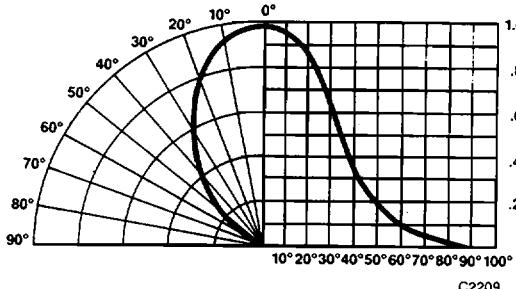
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

Power dissipation	87 mW
Operating temperature	-20°C to +100°C
Storage temperature	-55°C to +100°C
Lead soldering time at 260°C	5 seconds
Peak forward current (see Note 1)	300 mA
Reverse voltage (I _R = 100 μ A)	5V
Average forward current (see Note 2)	20 mA

NOTES

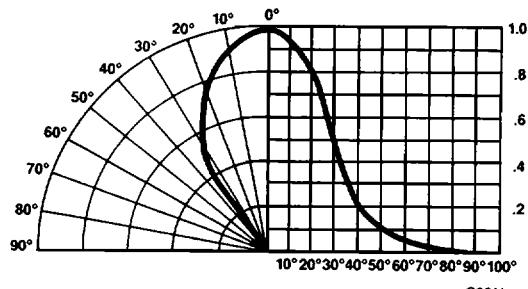
1. Maximum I_{peak} at f = 1 kHz, DF = 6.7%
2. Derate linearly as shown in Figure 4.

TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES
(25°C Free Air Temperature)

*Fig. 1. Relative Intensity
vs. Wavelength*

*Fig. 2. Forward Current vs.
Forward Voltage*

*Fig. 3. Relative Luminous Intensity
vs. DC Forward Current*

*Fig. 4. Maximum Forward DC Current
vs. Ambient Temperature. Derating
Based on $T_J\text{ MAX} = 110^\circ\text{C}$*

TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES
 (25°C Free Air Temperature) (Cont'd)


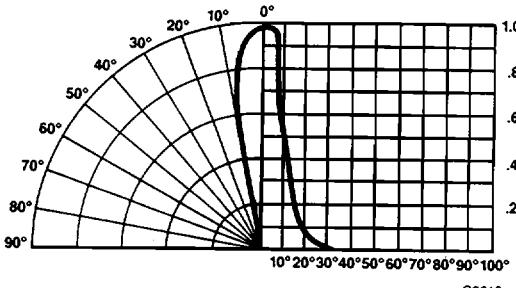
C2209

Fig. 5. Relative Luminous Intensity
vs. Angular Displacement.
HLMP-D150



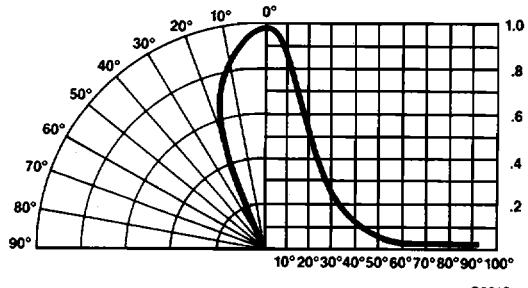
C2211

Fig. 6. Relative Luminous Intensity
vs. Angular Displacement.
HLMP-K150



C2210

Fig. 7. Relative Luminous Intensity
vs. Angular Displacement.
HLMP-D155



C2212

Fig. 8. Relative Luminous Intensity
vs. Angular Displacement.
HLMP-K155